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SGP10N60RUFD 600 V, 10 A Short Circuit Rated IGBT

General Description

Fairchild's RUFD series of Insulated Gate Bipolar Transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, Uninterrupted Power Supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Features

- 10 A, 600 V, T_C = 100°C
- Low Saturation Voltage: V_{CE}(sat) = 2.1 V @ I_C = 10 A
- High Speed Switching
- High Input Impedance
- Short Circuit Rating

Applications

Motor Control, UPS, General Inverter

	GCE	⁻ O-220
Absolute M	Aximum Ratings	T _C = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
1	Collector Current	@ $T_{C} = 25^{\circ}C$	16	A
С	Collector Current	@ T _C = 100°C	10	A
I _{СМ (1)}	Pulsed Collector Current		30	A
	Diode Continuous Forward Current	@ T _C = 25°C	24	A
F	Diode Continuous Forward Current	@ T _C = 100°C	12	A
FM	Diode Maximum Forward Current		92	A
T _{SC}	Short Circuit Withstand Time @ T _C = 100°C		10	us
D	Maximum Power Dissipation	@ $T_{C} = 25^{\circ}C$	75	W
	Maximum Power Dissipation	@ T _C = 100°C	30	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Second	ds	300	°C

Notes : (1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
R _{0JC} (IGBT)	Thermal Resistance, Junction-to-Case		1.6	°C/W
R _{0JC} (DIODE)	Thermal Resistance, Junction-to-Case		2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

1

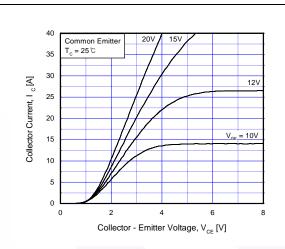


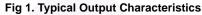


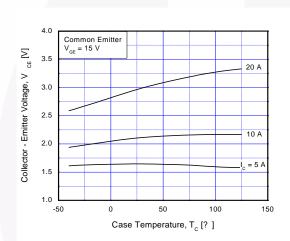


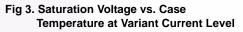
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Un
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 250 uA	600			V
$\frac{\Delta B_{VCES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0 V, I_{C} = 1 mA$		0.6		V/ª
ICES	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$			250	u/
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$			± 100	n/
On Cha	racteristics					
V _{GE(th)}	G-E Threshold Voltage	I _C = 10 mA, V _{CE} = V _{GE}	5.0	6.0	8.5	V
	Collector to Emitter	$I_{\rm C} = 10$ A, $V_{\rm GE} = 15$ V		2.2	2.8	v
V _{CE(sat)}	Saturation Voltage	$I_{\rm C} = 16 \text{ A}, V_{\rm GE} = 15 \text{ V}$		2.5		V
Dvnami	c Characteristics					
C _{ies}	Input Capacitance			660	1	pl
C _{oes}	Output Capacitance	$V_{CE} = 30 V, V_{GE} = 0 V,$		115		pi
C _{res}	Reverse Transfer Capacitance	f = 1 MHz		25		p. pf
t _{d(on)} t _r	Turn-On Delay Time Rise Time	-		15 30		ns ns
t _r				30		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_{C} = 10 \text{ A},$		36	50	ns
t _f	Fall Time	$R_{G} = 20 \Omega, V_{GE} = 15 V,$		158	200	ns
Eon	Turn-On Switching Loss	Inductive Load, T _C = 25°C		141		u
E _{off}	Turn-Off Switching Loss			215		u
Ets	Total Switching Loss			356	500	u
t _{d(on)}	Turn-On Delay Time			16		ns
t _r	Rise Time			33		ns
t _{d(off)}	Turn-Off Delay Time	$V_{\rm CC} = 300 \text{ V}, \text{ I}_{\rm C} = 10 \text{ A},$		42	60	ns
t _f	Fall Time	$R_{G} = 20 \Omega$, $V_{GE} = 15 V$,		242	350	ns
Eon	Turn-On Switching Loss	Inductive Load, T _C = 125°C		161		u
Eoff	Turn-Off Switching Loss			452		u
E _{ts}	Total Switching Loss			613	860	u
T _{sc}	Short Circuit Withstand Time	V _{CC} = 300 V, V _{GE} = 15 V @ T _C = 100°C	10			us
	Total Gate Charge	V _{CE} = 300 V, I _C = 10 A,		30	45	nC
Q _g	Total Gate Gharge		1		40	nC
	Gate-Emitter Charge			5	10	
Qg	, , , , , , , , , , , , , , , , , , ,	$V_{GE} = 15 V$		5 8	10	n

Symbol	Parameter	Test Condi	tions	Min.	Тур.	Max.	Unit	
V	Diode Forward Voltage	L = 12 A	$T_{C} = 25^{\circ}C$		1.4	1.7	V	
V _{FM}	Didde i diward voltage	I _F = 12 A	$T_{\rm C} = 100^{\circ}{\rm C}$		1.3		v	
+	Diode Reverse Recovery Time		$T_{C} = 25^{\circ}C$		42	60	ns	
۲r	Didde Reverse Recovery Time		$T_{\rm C} = 100^{\circ}{\rm C}$		60		115	
1	Diode Peak Reverse Recovery	I _F = 12 A,	$T_{C} = 25^{\circ}C$		3.5	6.0	А	
Irr	Current	di _F /dt=200 A/µs	$T_{C} = 100^{\circ}C$		5.6		~	
O Diodo Roy	Diode Reverse Recovery Charge		$T_{C} = 25^{\circ}C$		80	180	nC	
Q _{rr}	Didde Neverse Necovery Charge		T _C = 100°C		220			









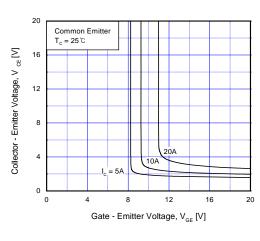


Fig 5. Saturation Voltage vs. $\rm V_{GE}$

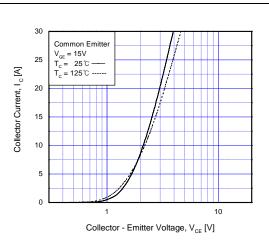


Fig 2. Typical Saturation Voltage Characteristics

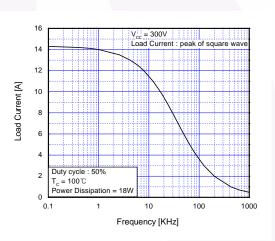


Fig 4. Load Current vs. Frequency

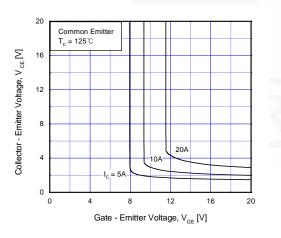
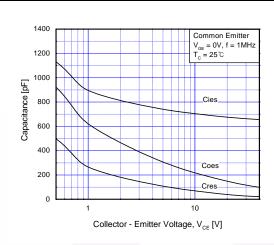
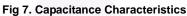
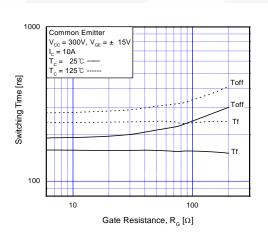
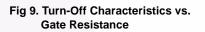


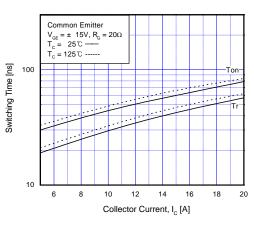
Fig 6. Saturation Voltage vs. $\rm V_{GE}$

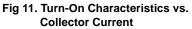


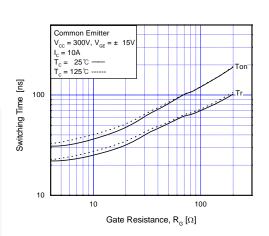


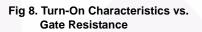












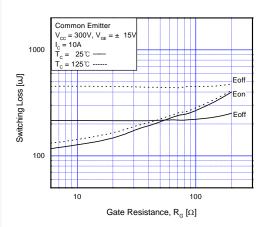
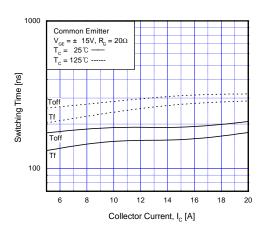
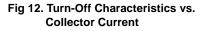
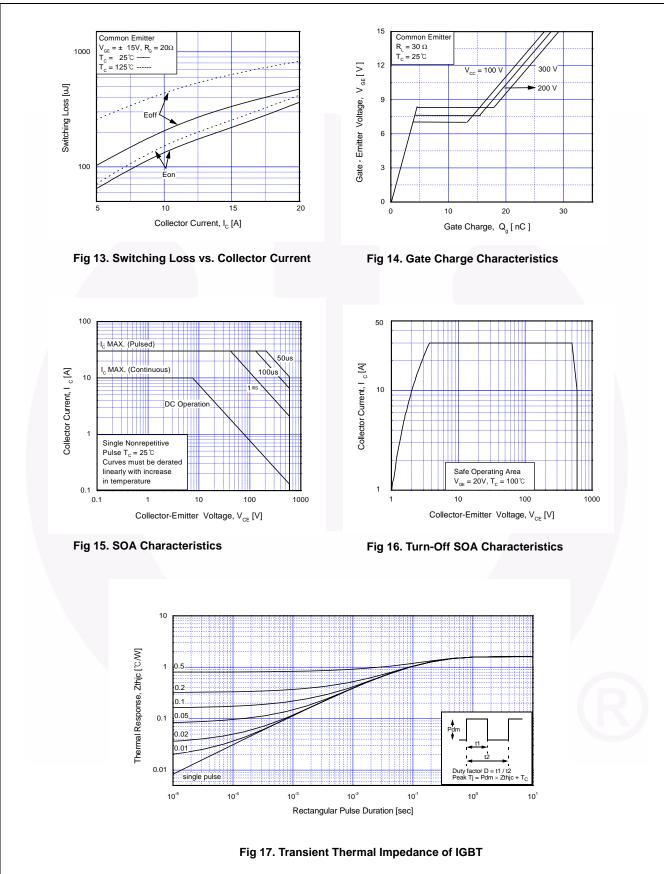


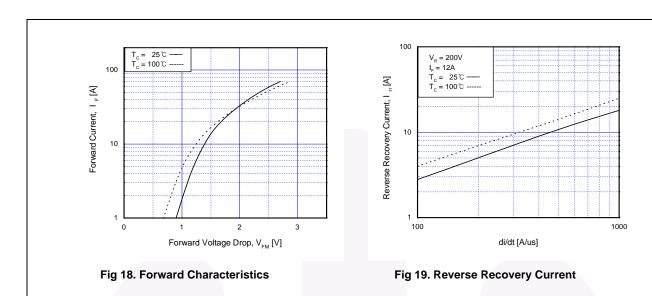
Fig 10. Switching Loss vs. Gate Resistance





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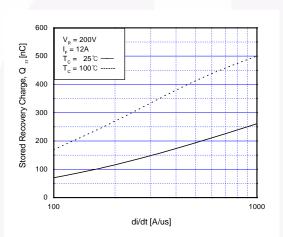
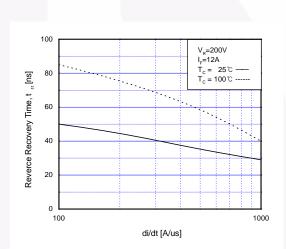
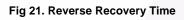


Fig 20. Stored Charge





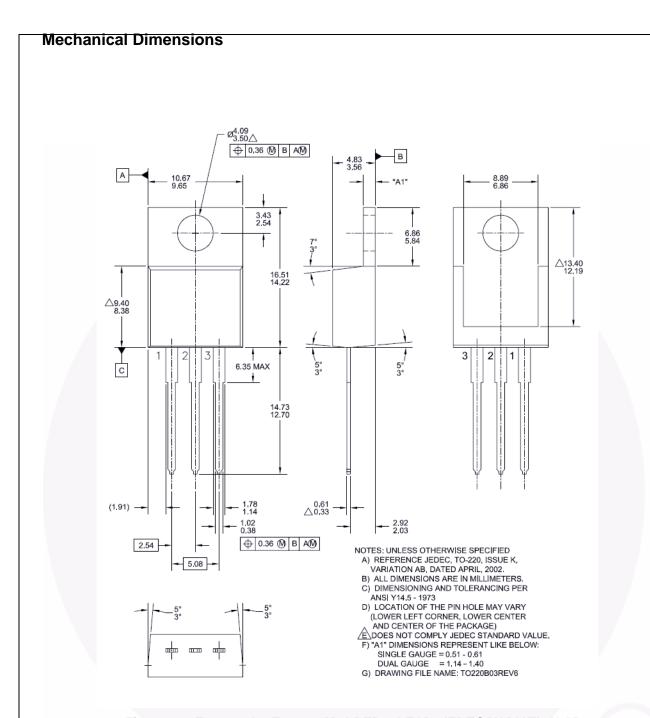


Figure 22. TO-220 3L - TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB

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